

MARKED-UP VERSION OF AMENDED CLAIMS

1. (Amended) A semiconductor structure comprising:
a substrate;
two or more adjacent conductors, disposed in at least one dielectric layer formed over said substrate and electrically isolated from each other, wherein each pair of adjacent conductors is separated by a gap; and
a first high dielectric constant material formed in the gap between two adjacent conductors.

7. (Amended) The semiconductor structure of Claim 1 wherein at least one pair of adjacent conductors comprises a power supply line [an] and a ground wire.

NEW VERSION OF CLAIMS WITH INCORPORATED AMENDMENTS

1. A semiconductor structure comprising:

a substrate;

two or more adjacent conductors, disposed in at least one dielectric layer formed over said substrate and electrically isolated from each other, wherein each pair of adjacent conductors is separated by a gap; and

a first high dielectric constant material formed in the gap between two adjacent conductors.

7. The semiconductor structure of Claim 1 wherein at least one pair of adjacent conductors comprises a power supply line and a ground wire.